Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Isolated plastic package
- Low leakage current
- · Low thermal resistance
- · Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- · Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values		Unit		
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			600			V
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 51$ °C; Fig. 1; Fig. 2; Fig. 3	20		А		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; $T_h \le$ 51 °C; square-wave pulse	40		А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	200 220		А		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions	M	lin	Тур	Max	Unit
Static ch	aracteristics		,				
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>	-		1.8	2.5	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>	-		1.2	1.6	V
Dynamic	characteristics	'	,				
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-		-	35	ns

5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol
K	cathode	mb	
А	anode		K — A
n.c.	mounting base; isolated		001aaa020
	K A	K cathode A anode	K cathode A anode n.c. mounting base; isolated

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BYC20X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113				

7. Marking

Table 4. Marking codes

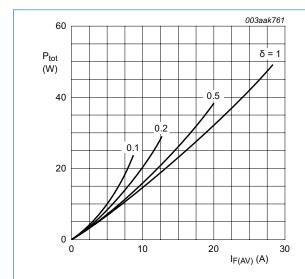
Type number	Marking codes
BYC20X-600P	BYC20X-600P

8. Limiting values

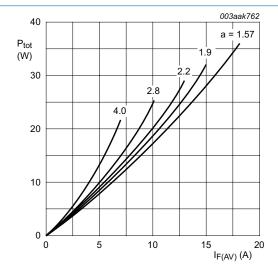
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 51$ °C; Fig. 1; Fig. 2; Fig. 3	20	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 51 °C$; square-wave pulse	40	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	200	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_o &= 1.311 \text{ V; R}_s = 0.015 \text{ }\Omega \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.311 V; R_s = 0.015 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

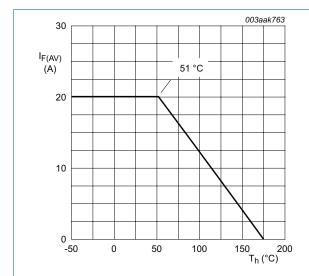


Fig. 3. Forward current as a function of heatsink temperature; maximum values

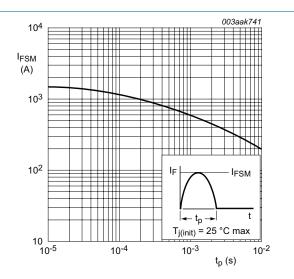
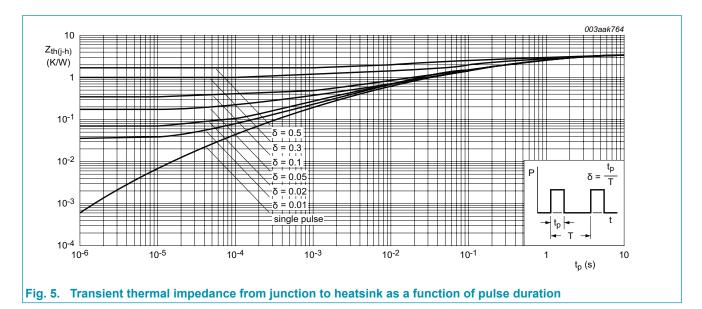


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	3.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Isolation characteristics

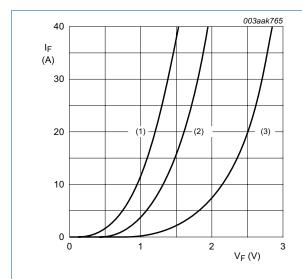
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	IV	lin	Тур	Max	Unit
Static cha	racteristics						
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>	-		1.8	2.5	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>	-		1.2	1.6	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-		-	10	μA
		V _R = 600 V; T _j = 150 °C	-		-	600	μA
Dynamic	characteristics				,	,	,
t _{rr}	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } Fig. 7$	-		-	35	ns
		$I_F = 20 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-		32	-	ns
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-		55	-	ns
I _{RM} peak reverse reco	peak reverse recovery current	$I_F = 20 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-		2.9	-	А
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-		8	-	А
Q _r	recovered charge	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-		50	-	nC
		$I_F = 20 \text{ A; } V_R = 200 \text{ V; } dI_F/dt = 200 \text{ A/µs;}$ $T_i = 125 \text{ °C; } \frac{\text{Fig. 7}}{\text{C}}$	-		220	-	nC



 V_o = 1.311 V; R_s = 0.015 Ω

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values



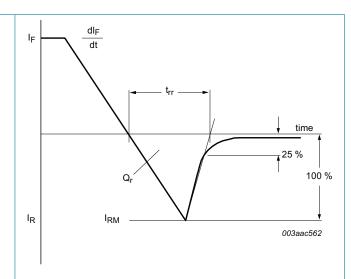
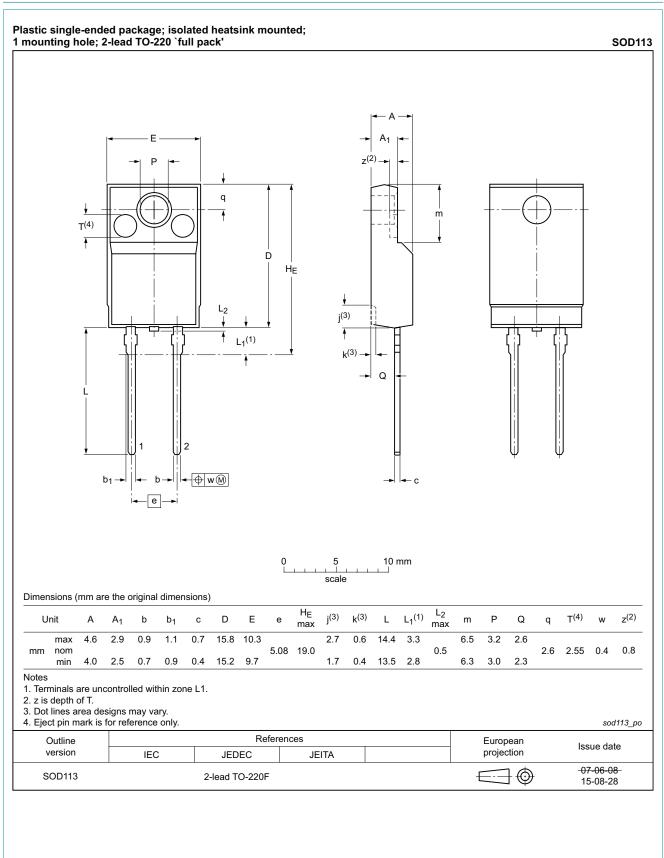


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



BYC20X-600P

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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